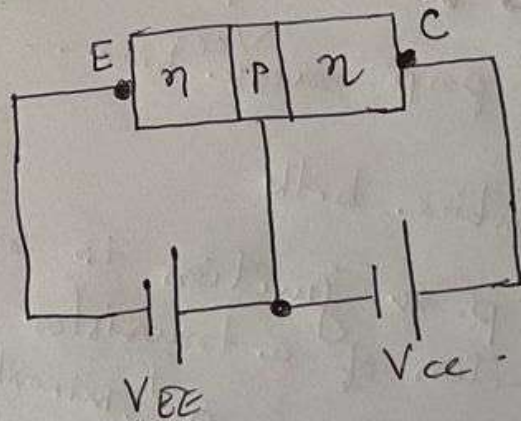
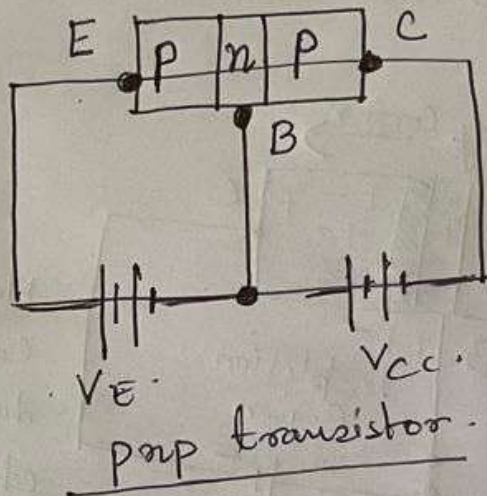


BJT (Bipolar Junction Transistors)

(1)

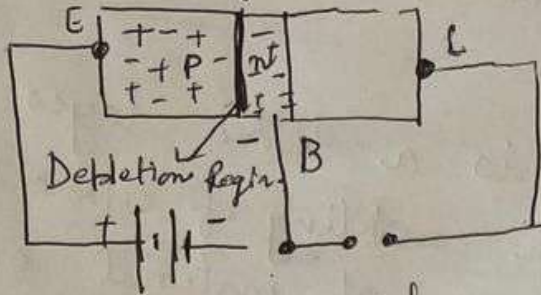
The transistor is a three-layer semiconductor device consisting of either two n-type and one p-type layers of material or two p-type and one n-type layers of material, called npn transistor and pnp transistor.



Transistor Operation

The operation of npn transistor is exactly the same if the roles played by the e^- s and holes are interchanged.

Majority Carriers

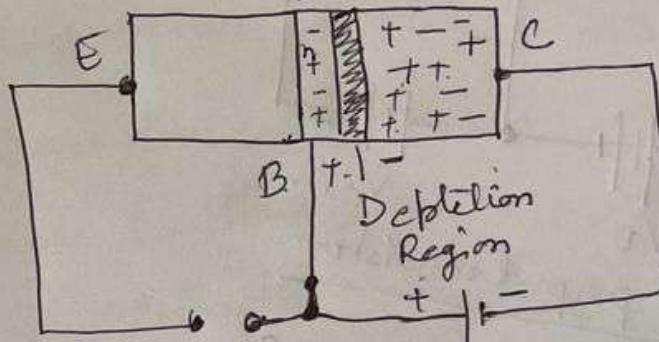


PNP-transistor.
Forward Bias.

Due to forward bias the depletion region has been reduced in width resulting a heavy flow of majority carriers from the p- to n-type material.

Let us now remove the base to emitter bias of the PNP transistor.

Minority Carriers



PNP - reverse bias.

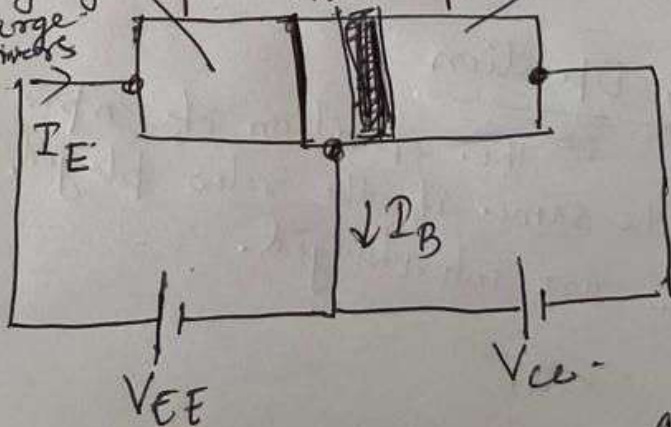
Here the conduction is due to minority charge carriers.

If we combine both

One p-n junction is reverse biased while the other junction of a transistor is forward biased.

Majority charge carriers

minority charge carrier.



Majority and minority charge carrier flow of a PNP transistor.

$$I_E = I_C + I_B$$

$$I_C = I_{C_{\text{majority}}} + I_{C_{\text{minority}}}$$

The minority-current component is called the leakage current and is given the symbol I_{CO} i.e.

I_C currents with emitter terminal open.

Three configurations of BJT are

- ① Common Base.
- ② Common Emitter
- ③ Common - collector.